

East & USPBUSPT, WPID, JPO

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	53890	implant\$.clm.	US-PGPUB; USPAT	OR	OFF	2005/09/28 15:50
L2	678821	(etch\$ or patern\$ or remov\$).clm.	US-PGPUB; USPAT	OR	OFF	2005/09/28 15:50
L3	157072	(imaging or mask or photomask or resist or photoresist).clm.	US-PGPUB; USPAT	OR	ON	2005/09/28 15:51
L4	8226	1 and 2 and 3	US-PGPUB; USPAT	OR	ON	2005/09/28 15:39
L5	5850	1 with 3	US-PGPUB; USPAT	OR	ON	2005/09/28 15:39
L6	36838	2 with 3	US-PGPUB; USPAT	OR	ON	2005/09/28 15:39
L7	2968	4 and 5 and 6	US-PGPUB; USPAT	OR	ON	2005/09/28 15:39
L8	206599	semiconduct\$.clm.	US-PGPUB; USPAT	OR	ON	2005/09/28 15:40
L9	2273	7 and 8	US-PGPUB; USPAT	OR	ON	2005/09/28 15:40
L10	24955	2 with 8	US-PGPUB; USPAT	OR	ON	2005/09/28 15:40
L11	1024	9 and 10	US-PGPUB; USPAT	OR	ON	2005/09/28 15:40
L12	3784	1 with (peak or concentration).clm.	US-PGPUB; USPAT	OR	ON	2005/09/28 15:51
L13	199	11 and 12	US-PGPUB; USPAT	OR	ON	2005/09/28 15:41
L14	565	1 with peak.clm.	US-PGPUB; USPAT	OR	ON	2005/09/28 15:41
L15	26	13 and 14	US-PGPUB; USPAT	OR	ON	2005/09/28 15:42
L16	574	1 with (peak or concentration).clm. with 3	US-PGPUB; USPAT	OR	ON	2005/09/28 15:43
L17	13	15 and 16	US-PGPUB; USPAT	OR	ON	2005/09/28 15:45
L18	14748	micron.as.	US-PGPUB; USPAT	OR	ON	2005/09/28 15:45
L19	13	16 and 18	US-PGPUB; USPAT	OR	ON	2005/09/28 15:45
L20	202199	implant\$	US-PGPUB; USPAT	OR	OFF	2005/09/28 16:00
L21	2518520	(etch\$ or patern\$ or remov\$)	US-PGPUB; USPAT	OR	OFF	2005/09/28 16:01
L22	649662	(imaging or mask or photomask or resist or photoresist)	US-PGPUB; USPAT	OR	ON	2005/09/28 16:01

L23	1099495	peak or concentration	US-PGPUB; USPAT	OR	ON	2005/09/28 16:01
L24	4238	20 with 23 with 22	US-PGPUB; USPAT	OR	ON	2005/09/28 15:51
L25	168254	21 with 22	US-PGPUB; USPAT	OR	ON	2005/09/28 15:52
L26	1475	24 same 25	US-PGPUB; USPAT	OR	ON	2005/09/28 15:52
L27	1475	20 same 21 same 22 same 23 same 26	US-PGPUB; USPAT	OR	ON	2005/09/28 15:53
L28	1062262	semiconduct\$ or silicon or si or poly or polysi\$ or gallium or gaas or inp	US-PGPUB; USPAT	OR	ON	2005/09/28 16:01
L29	178295	21 with 28	US-PGPUB; USPAT	OR	ON	2005/09/28 15:54
L30	178295	28 same 29	US-PGPUB; USPAT	OR	ON	2005/09/28 15:55
L31	749	27 same 30	US-PGPUB; USPAT	OR	ON	2005/09/28 15:56
L32	10588	blanket\$ with 21	US-PGPUB; USPAT	OR	ON	2005/09/28 15:56
L33	11040	"etch\$ back\$"	US-PGPUB; USPAT	OR	ON	2005/09/28 15:56
L34	21	31 same (32 or 33)	US-PGPUB; USPAT	OR	ON	2005/09/28 15:57
L35	109430	implant\$	JPO; DERWENT	OR	OFF	2005/09/28 16:00
L36	449305	(imaging or mask or photomask or resist or photoresist)	JPO; DERWENT	OR	ON	2005/09/28 16:01
L37	538560	peak or concentration	JPO; DERWENT	OR	ON	2005/09/28 16:01
L38	2635473	semiconduct\$ or silicon or si or poly or polysi\$ or gallium or gaas or inp	JPO; DERWENT	OR	ON	2005/09/28 16:01
L39	1705491	(etch\$ or patern\$ or remov\$)	JPO; DERWENT	OR	OFF	2005/09/28 16:02
L40	2314	35 and 36 and 37 and 38 and 39	JPO; DERWENT	OR	OFF	2005/09/28 16:02
L41	15771	35 with 36	JPO; DERWENT	OR	OFF	2005/09/28 16:02
L42	106104	36 with 39	JPO; DERWENT	OR	OFF	2005/09/28 16:02
L43	147610	39 with 38	JPO; DERWENT	OR	OFF	2005/09/28 16:02
L44	731	40 and 41 and 42 and 43	JPO; DERWENT	OR	OFF	2005/09/28 16:03

L45	1545	39 with blanket\$	JPO; DERWENT	OR	OFF	2005/09/28 16:03
L46	2084	"etch\$ back"	JPO; DERWENT	OR	OFF	2005/09/28 16:03
L47	5	44 and (45 or 46)	JPO; DERWENT	OR	OFF	2005/09/28 16:04
L48	948059	develop\$ or solubit\$ or solvent	JPO; DERWENT	OR	ON	2005/09/28 16:04
L49	222	41 with 48	JPO; DERWENT	OR	ON	2005/09/28 16:05
L50	158	49 and 42	JPO; DERWENT	OR	ON	2005/09/28 16:05
L51	81	43 and 50	JPO; DERWENT	OR	ON	2005/09/28 16:05